

C1
correct perform pixel control, conventionally performed by a driver circuit external to the substrate, by a driver circuit formed on the same substrate as the pixel.

[On page 2, please replace the third full paragraph with the following.

C2
As a technology for solving such a problem, a technique of forming EL layers by an ink jet method is suggested. For example, an active matrix EL display in which EL layers are formed using an ink jet method is disclosed in Japanese Patent Application Laid-Open No. Hei 10-012377. Further, a similar technique is also disclosed in Shimoda, T. et al., SID 99 DIGEST, P376-9, "Multicolor Pixel Patterning of Light-Emitted Polymers by Ink-Jet Printing."

[On page 14, please replace the second full paragraph with the following.

C3
Further, by making the passivation film 41 possess a heat radiation effect, it is also effective in preventing thermal degradation of the EL layer. Note that light is emitted from the base 11 side in the Fig. 1 structure of the EL display device, and therefore it is necessary for the passivation film 41 to have light transmitting characteristics. In addition, in a case of using an organic material for the EL layer, it deteriorates by bonding with oxygen, so it is preferable not to use an insulating film that easily releases oxygen.

[On page 19, please replace the third full paragraph with the following.

C4
After banks 101a and 101b are formed, an EL layer 47 is next formed (an organic material is preferable). The EL layer may be used by a single layer or by a laminate structure, but there are more cases in which a laminate structure is used. Though various laminate structures are suggested by combining an emitting layer, an electron transporting layer, an electron injecting layer, a hole injecting layer, a hole transporting

C4
concl layer, any structure is acceptable in the present invention. Further, a fluorescent dye, etc.
may be doped in the EL layer.

[On pages 31-32, please replace the third full paragraph beginning at line 20 with the following:

C5
Next, as shown in Fig. 3C, the protecting film 303 is removed, and activation of the added periodic table group V element is performed. A known technique of activation may be used as the means of activation, and activation is done in embodiment 1 by irradiation of excimer laser light. Both of pulse emission type laser and a continuous emission type laser may be used, and it is not necessary to place any limits on the use of excimer laser light. The goal is the activation of the added impurity element, and it is preferable that irradiation is performed at an energy level at which the crystallization silicon film does not melt. Note that the laser irradiation may also be performed with the protecting film 303 in place.

[**IN THE CLAIMS:**

Please amended claims 1-5, 7, 10, 21, 30-35 as follows. While claims 1, 6, 11, 30, and 34 are presented below in their amended form, the amendments to the above-noted claims are outlined in an Attachment to the Amendment using the conventional indication method of bracketing and underlining.

C6
D1
1. (Amended) A method for manufacturing an electrical device, said method comprising the steps of:

forming at least a thin film transistor on an insulating surface;

forming an insulating film over the thin film transistor;

forming a pixel electrode over the insulating film, said pixel electrode being connected to the thin film transistor;

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